

Silicon PNP Power Transistors

2SB760

DESCRIPTION

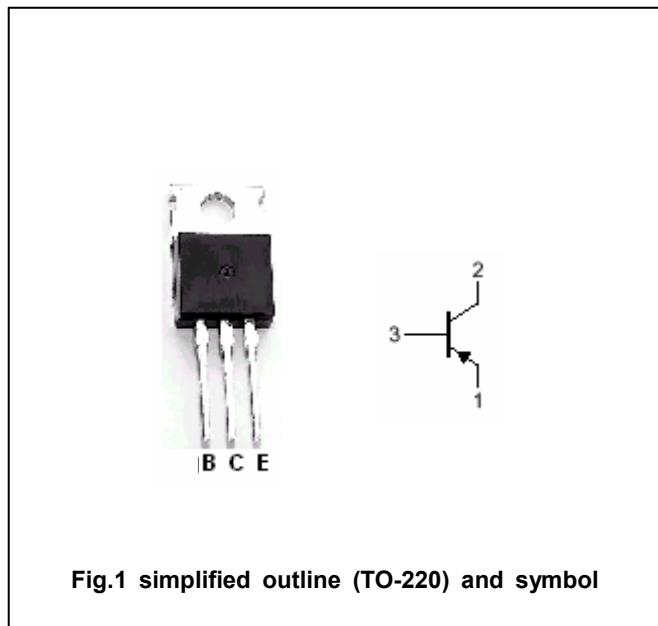
- With TO-220 package
- Low collector saturation voltage
- Complement to type 2SD855

APPLICATIONS

- For audio frequency and radio frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-60	V
V_{CEO}	Collector-emitter voltage	Open base	-60	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-1	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	30	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA I _B =0	-60			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-1mA; I _E =0	-60			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-1mA; I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-1A; I _B =-0.1A			-1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-1A; I _B =-0.1A			-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-60V; I _E =0			-100	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-100	μA
h _{FE}	DC current gain	I _C =-0.2A ; V _{CE} =-4V	40		450	

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PACKAGE OUTLINE

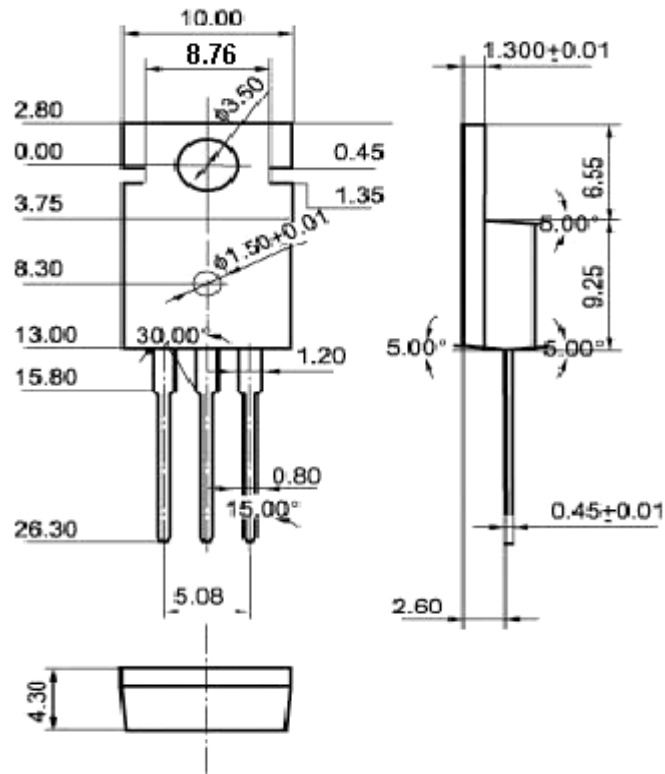


Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)